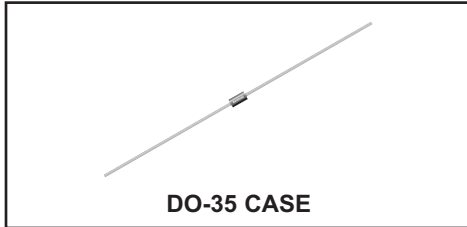


CDSH270
SILICON SCHOTTKY DIODE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CDSH270 silicon Schottky diode is designed to replace the 1N270 Germanium diode. Some advantages over the 1N270 are lower forward voltage, lower leakage current, faster switching speed, and a more robust package.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Peak Repetitive Reverse Voltage
 Continuous Forward Current
 Peak Repetitive Forward Current
 Peak Forward Surge Current, $t_p=10\text{ms}$
 Power Dissipation
 Operating Junction Temperature
 Storage Temperature
 Thermal Resistance

SYMBOL

V_{RRM} 100
 I_F 100
 I_{FRM} 350
 I_{FSM} 750
 P_D 100
 T_J -65 to +125
 T_{stg} -65 to +150
 θ_{JA} 300

UNITS

V
 mA
 mA
 mA
 mW
 $^\circ\text{C}$
 $^\circ\text{C}$
 $^\circ\text{C/W}$

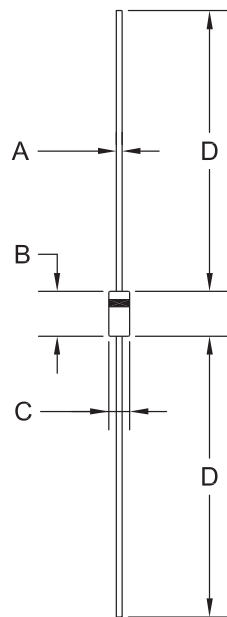
ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	TYP	MAX	UNITS
I_R	$V_R=50\text{V}$		100	nA
I_R	$V_R=50\text{V}, T_A=100^\circ\text{C}$		20	μA
V_F	$I_F=1.0\text{mA}$		0.45	V
V_F	$I_F=100\text{mA}$	0.9		V
V_F	$I_F=200\text{mA}$		1.0	V
C_J	$V_R=10\text{V}, f=1.0\text{MHz}$	1.2		pF

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DO-35 CASE - MECHANICAL OUTLINE



DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.018	0.022	0.46	0.56
B	0.120	0.200	3.05	5.08
C	0.060	0.090	1.52	2.29
D	1.000	-	25.40	-

DO-35 (REV: R1)

MARKING: FULL PART NUMBER

R1

R1 (16-August 2012)